

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MZ541FK

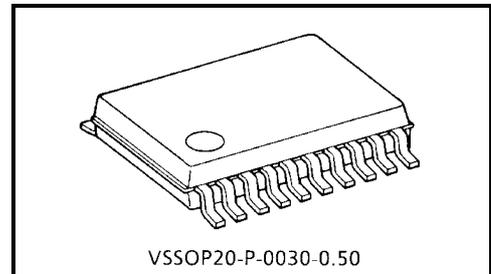
Low Voltage Octal Bus Buffer with 5 V Tolerant Inputs and Outputs

The TC7MZ541FK is a high performance CMOS octal bus buffer. Designed for use in 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3 V) VCC applications, but it could be used to interface to 5 V supply environment for both inputs and outputs.

The TC7MZ541FK is a non-inverting 3-state buffer having two active-low output enables. When either $\overline{OE}1$ or $\overline{OE}2$ are high, the terminal outputs are in the high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.



VSSOP20-P-0030-0.50

Weight: 0.03 g (typ.)

Features

- Low voltage operation: $V_{CC} = 2.0\sim 3.6$ V
- High speed operation: $t_{pd} = 6.5$ ns (max) ($V_{CC} = 3.0\sim 3.6$ V)
- Output current: $|I_{OH}|/I_{OL} = 24$ mA (min) ($V_{CC} = 3.0$ V)
- Latch-up performance: ± 500 mA
- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Pin and function compatible with the 74 series (74AC/VHC/HC/F/ALS/LS etc.) 541 type.

000630EBA1

• TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

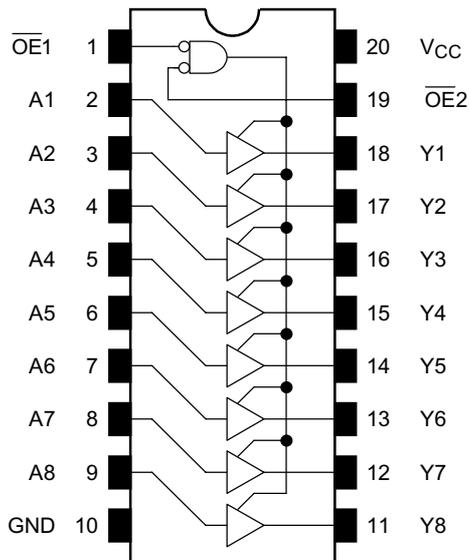
• The Toshiba products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These Toshiba products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of Toshiba products listed in this document shall be made at the customer's own risk.

• The products described in this document are subject to the foreign exchange and foreign trade laws.

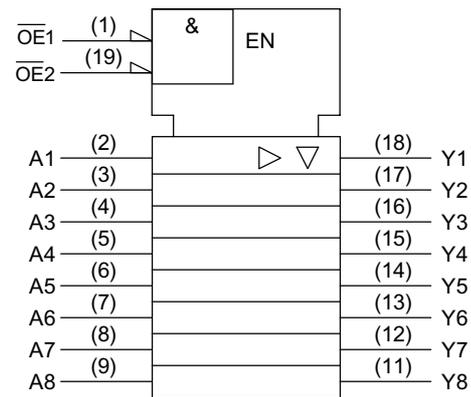
• The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

• The information contained herein is subject to change without notice.

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inputs			Outputs
$\overline{OE1}$	$\overline{OE2}$	A_n	
H	X	X	Z
X	H	X	Z
L	L	H	H
L	L	L	L

X: Don't care

Z: High impedance

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5~7.0	V
DC input voltage	V_{IN}	-0.5~7.0	V
DC output voltage	V_{OUT}	-0.5~7.0 (Note1)	V
		-0.5~ $V_{CC} + 0.5$ (Note2)	
Input diode current	I_{IK}	-50	mA
Output diode current	I_{OK}	±50 (Note3)	mA
DC output current	I_{OUT}	±50	mA
Power dissipation	P_D	180	mW
DC V_{CC} /ground current	I_{CC}/I_{GND}	±100	mA
Storage temperature	T_{stg}	-65~150	°C

Note1: Output in off-state

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2.0~3.6	V
		1.5~3.6 (Note4)	
Input voltage	V_{IN}	0~5.5	V
Output voltage	V_{OUT}	0~5.5 (Note5)	V
		0~ V_{CC} (Note6)	
Output current	I_{OH}/I_{OL}	± 24 (Note7)	mA
		± 12 (Note8)	
Operating temperature	T_{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note9)	ns/V

Note4: Data retention only

Note5: Output in off-state

Note6: High or low state

Note7: $V_{CC} = 3.0\sim 3.6$ V

Note8: $V_{CC} = 2.7\sim 3.0$ V

Note9: $V_{IN} = 0.8\sim 2.0$ V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC Characteristics ($T_a = -40\sim 85^\circ\text{C}$)

Characteristics		Symbol	Test Condition	V_{CC} (V)	Min	Max	Unit	
Input voltage	High level	V_{IH}	—	2.7~3.6	2.0	—	V	
	Low level	V_{IL}	—	2.7~3.6	—	0.8		
Output voltage	High level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	2.7~3.6	$V_{CC} - 0.2$	—	V
				$I_{OH} = -12 \text{ mA}$	2.7	2.2	—	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	—	
				$I_{OH} = -24 \text{ mA}$	3.0	2.2	—	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	2.7~3.6	—	0.2	
				$I_{OL} = 12 \text{ mA}$	2.7	—	0.4	
				$I_{OL} = 16 \text{ mA}$	3.0	—	0.4	
				$I_{OL} = 24 \text{ mA}$	3.0	—	0.55	
Input leakage current	I_{IN}	$V_{IN} = 0\sim 5.5$ V		2.7~3.6	—	± 5.0	μA	
3-state output off-state current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0\sim 5.5$ V		2.7~3.6	—	± 5.0	μA	
Power off leakage current	I_{OFF}	$V_{IN}/V_{OUT} = 5.5$ V		0	—	10.0	μA	
Quiescent supply current	I_{CC}	$V_{IN} = V_{CC}$ or GND		2.7~3.6	—	10.0	μA	
		$V_{IN}/V_{OUT} = 3.6\sim 5.5$ V		2.7~3.6	—	± 10.0		
Increase in I_{CC} per input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6$ V		2.7~3.6	—	500		

AC Characteristics (Ta = -40~85°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.7	—	7.5	ns
	t _{pHL}		3.3 ± 0.3	1.5	6.5	
Output enable time	t _{pZL}	Figure 1, Figure 3	2.7	—	9.5	ns
	t _{pZH}		3.3 ± 0.3	1.5	8.5	
Output disable time	t _{pLZ}	Figure 1, Figure 3	2.7	—	8.5	ns
	t _{pHZ}		3.3 ± 0.3	1.5	7.5	
Output to output skew	t _{osLH}	(Note10)	2.7	—	—	ns
	t _{osHL}		3.3 ± 0.3	—	1.0	

Note10: This parameter is guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics

(Ta = 25°C, Input: t_r = t_f = 2.5 ns, C_L = 50 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit	
Quiet output maximum dynamic	V _{OL}	V _{OLP}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V
Quiet output minimum dynamic	V _{OL}	V _{OLV}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V

Capacitive Characteristics (Ta = 25°C)

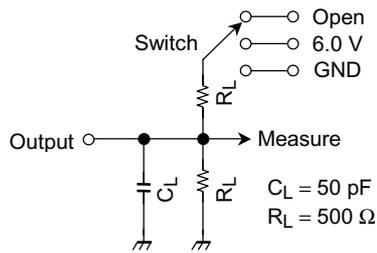
Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit	
Input capacitance	C _{IN}	—	3.3	7	pF	
Output capacitance	C _{OUT}	—	3.3	8	pF	
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note11)	3.3	40	pF

Note11: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

AC Test Circuit



Parameter	Switch
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V
t_{pHZ}, t_{pZH}	GND

Figure 1

AC Waveform

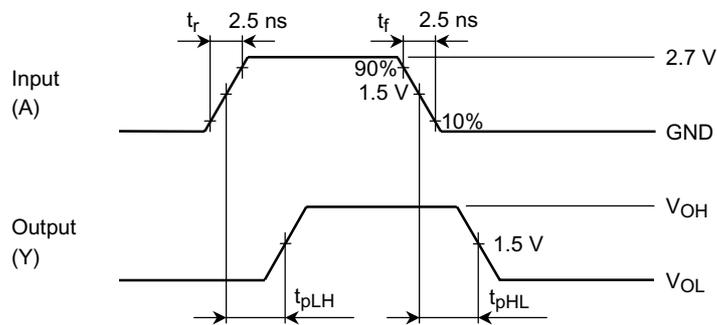


Figure 2 t_{pLH}, t_{pHL}

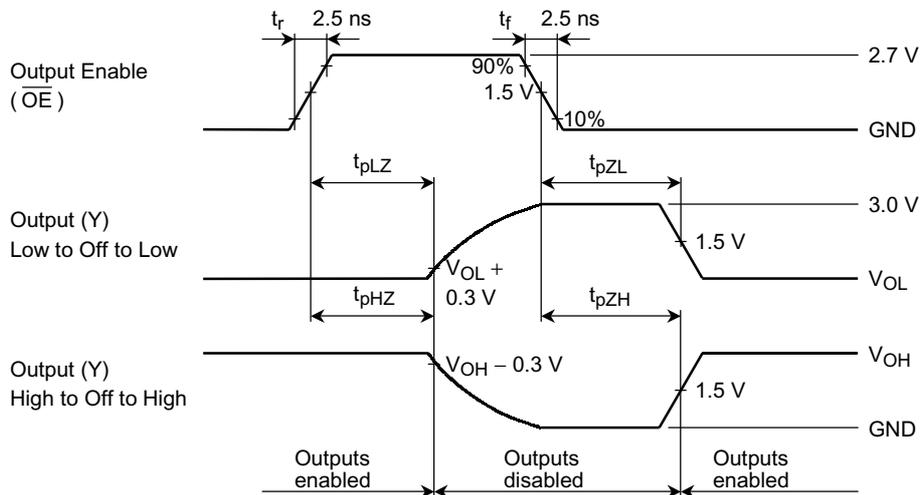
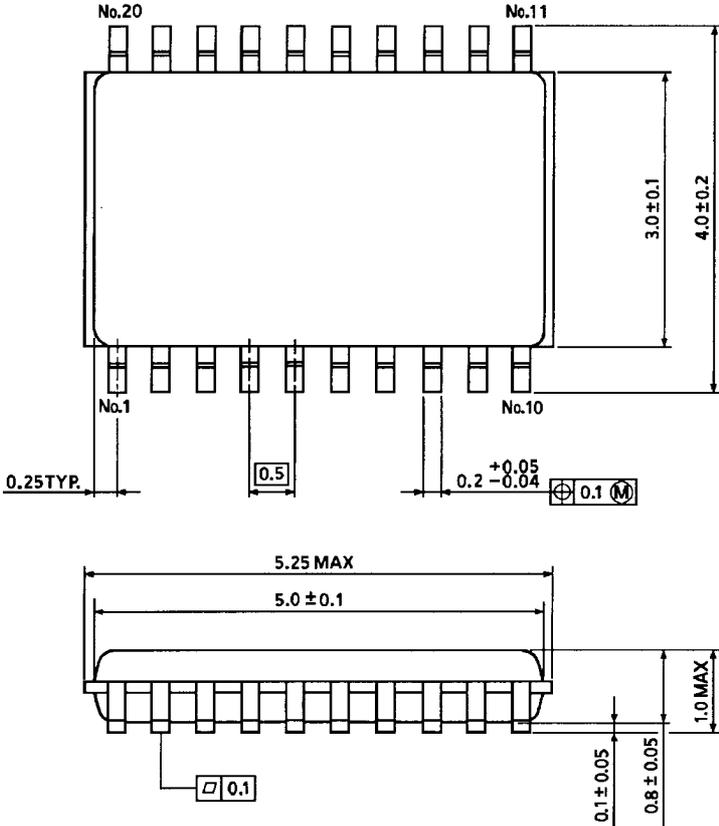


Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Package Dimensions

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)